

CY54/74FCT157T

SCCS014 - May 1994 - Revised February 2000

Quad 2-Input Multiplexer

Features

- Function, pinout, and drive compatible with FCT and F logic
- FCT-C speed at 4.3 ns max. (Com'l), FCT-A speed at 5.0 ns max. (Com'l)
- Reduced V_{OH} (typically = 3.3V) versions of equivalent FCT functions
- Edge-rate control circuitry for significantly improved noise characteristics
- Power-off disable feature
- · Matched rise and fall times
- Fully compatible with TTL input and output logic levels
- ESD > 2000V
- Extended commercial range of -40°C to +85°C

• Sink current 64 mA (Com'l),

32 mA (Mil)
Source current 32 mA (Com'l),
12 mA (Mil)

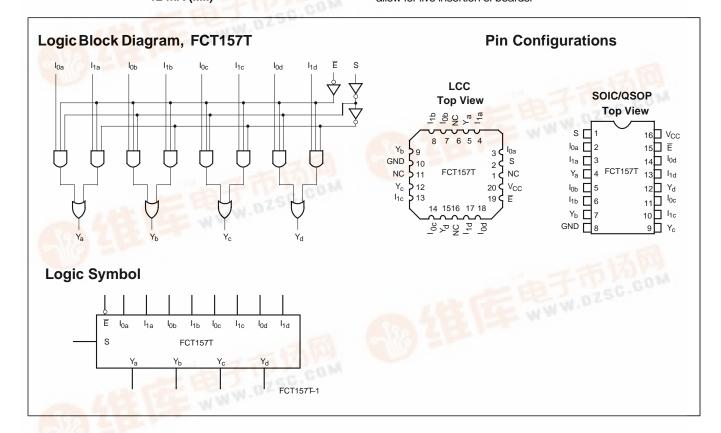
Functional Description

The FCT157T is a quad two-input multiplexer that selects four bits of data from two sources under the control of a common data Select input (S). The Enable input (\overline{E}) is Active LOW. When (\overline{E}) is HIGH, all of the outputs (Y) are forced LOW regardless of all other input conditions.

Moving data from two groups of registers to four common output buses is a common use of the FCT157T. The state of the Select input determines the particular register from which the data comes. It can also be used as a function generator. The device is useful for implementing highly irregular logic by generating any four of the sixteen different functions of two variables with one variable common.

The FCT157T is a logic implementation of a four-pole, two-position switch where the position of the switch is determined by the logic levels supplied to the Select input.

The outputs are designed with a power-off disable feature to allow for live insertion of boards.







Pin Description

Name	Description
S	Common Select Input
Ē	Enable Inputs (Active LOW)
I ₀	Data Inputs from Source 0
I ₁	Data Inputs from Source 1
Υ	Non-Inverted Output

Function Table^[1]

	Inp	Outputs		
E	S	I ₀	I ₁	Y
Н	Х	Х	Х	L
L	Н	Х	L	L
L	Н	Х	Н	Н
L	L	L	Х	L
L	L	Н	Х	Н

Maximum Ratings^[2,3]

(Above which the useful life may be impaired. For user guidelines, not tested.)
Storage Temperature65°C to +150°C
Ambient Temperature with Power Applied65°C to +135°C
Supply Voltage to Ground Potential0.5V to +7.0V
DC Input Voltage0.5V to +7.0V
DC Output Voltage0.5V to +7.0V
DC Output Current (Maximum Sink Current/Pin) 120 mA
Power Dissipation
Static Discharge Voltage>2001V (per MIL-STD-883, Method 3015)

Operating Range

Range	Range	Ambient Temperature	v _{cc}
Commercial	All	-40°C to +85°C	5V ± 5%
Military ^[4]	All	−55°C to +125°C	5V ± 10%

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Condition	Min.	Typ. ^[5]	Max.	Unit	
V _{OH}	Output HIGH Voltage	V _{CC} =Min., I _{OH} =-32 mA	Com'l	2.0			V
		V _{CC} =Min., I _{OH} =-15 mA	Com'l	2.4	3.3		V
		V _{CC} =Min., I _{OH} =-12 mA	Mil	2.4	3.3		V
V _{OL}	Output LOW Voltage	V _{CC} =Min., I _{OL} =64 mA	Com'l		0.3	0.55	V
		V _{CC} =Min., I _{OL} =32 mA	Mil		0.3	0.55	V
V _{IH}	Input HIGH Voltage		'	2.0			V
V _{IL}	Input LOW Voltage					0.8	V
V _H	Hysteresis ^[6]	All inputs		0.2		V	
V _{IK}	Input Clamp Diode Voltage	V _{CC} =Min., I _{IN} =-18 mA		-0.7	-1.2	V	
I _I	Input HIGH Current	V _{CC} =Max., V _{IN} =V _{CC}				5	μΑ
I _{IH}	Input HIGH Current	V _{CC} =Max., V _{IN} =2.7V				±1	μΑ
I _{IL}	Input LOW Current	V _{CC} =Max., V _{IN} =0.5V				±1	μΑ
I _{OZH}	Off State HIGH-Level Output Current	$V_{CC} = Max., V_{OUT} = 2.7V$				10	μА
I _{OZL}	Off State LOW-Level Output Current	$V_{CC} = Max., V_{OUT} = 0.5V$				-10	μА
los	Output Short Circuit Current ^[7]	V _{CC} =Max., V _{OUT} =0.0V		-60	-120	-225	mA
I _{OFF}	Power-Off Disable	V _{CC} =0V, V _{OUT} =4.5V				±1	μΑ

Note:

- H = HIGH Voltage Level. L = LOW Voltage Level. X = Don't Care
 Unless otherwise noted, these limits are over the operating free-air temperature range.
 Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground.

 T_A is the "instant on" case temperature.
 Typical values are at V_{CC}=5.0V, T_A=+25°C ambient.
 This parameter is specified but not tested.
 Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parametric tests. In any sequence of parameter tests, I_{OS} tests should be performed last.



Capacitance^[6]

Parameter	Description	Typ. ^[5]	Max.	Unit
C _{IN}	Input Capacitance	5	10	pF
C _{OUT}	Output Capacitance	9	12	pF

Power Supply Characteristics

Parameter	Description	Test Conditions	Typ. ^[5]	Max.	Unit
I _{CC}	Quiescent Power Supply Current	V _{CC} =Max., V _{IN} ≤0.2V, V _{IN} ≥V _{CC} -0.2V	0.1	0.2	mA
Δl _{CC}	Quiescent Power Supply Current (TTL inputs HIGH)	V _{CC} =Max., V _{IN} =3.4V, ^[8] f ₁ =0, Outputs Open	0.5	2.0	mA
I _{CCD}	Dynamic Power Supply Current ^[9]	V _{CC} =Max., One Input Toggling, 50% Duty Cycle, Outputs Open, OE=GND, V _{IN} ≤0.2V or V _{IN} ≥V _{CC} −0.2V	0.06	0.12	mA/MHz
Ic	Total Power Supply Current ^[10]	V_{CC} =Max., 50% Duty Cycle, Outputs Open, One Input Toggling at f_1 =10 MHz, \overline{OE} =GND, V_{IN} ≤0.2V or V_{IN} ≥ V_{CC} -0.2V	0.7	1.4	mA
		V _{CC} =Max., 50% Duty Cycle, Outputs Open, One Input Toggling at f ₁ =10 MHz, OE=GND, V _{IN} =3.4V or V _{IN} =GND	1.0	2.4	mA
		V_{CC} =Max., 50% Duty Cycle, Outputs Open, Four Bits Toggling at f ₁ =2.5 MHz, $\overline{\text{OE}}$ =GND, V_{IN} ≤0.2V or V_{IN} ≥ V_{CC} -0.2V	0.7	1.4 ^[11]	mA
		V _{CC} =Max., 50% Duty Cycle, Outputs Open, Four Bits Toggling at f ₁ =2.5 MHz, OE=GND, V _{IN} =3.4V or V _{IN} =GND	1.7	5.4 ^[11]	mA

Notes:

8. Per TTL driven input (V_{IN}=3.4V); all other inputs at V_{CC} or GND.

9. This parameter is not directly testable, but is derived for use in Total Power Supply calculations.

10. I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}
I_C = I_{CC}+ΔI_{CC}D_HN_T+I_{CCD}(f₀/2 + f₁N₁)
I_{CC} = Quiescent Current with CMOS input levels

ΔI_{CC} = Power Supply Current for a TTL HIGH input (V_{IN}=3.4V)
D_H = Duty Cycle for TTL inputs HIGH
N_T = Number of TTL inputs at D_H
I_{CC} = Dynamic Current caused by an input transition pair (HI H or I HI)

ICCD = Dynamic Current caused by an input transition pair (HLH or LHL)

= Clock frequency for registered devices, otherwise zero

T₀ = Clock frequency for registered devices, otherwise zero
 f₁ = Input signal frequency
 N₁ = Number of inputs changing at f₁
 All currents are in milliamps and all frequencies are in megahertz.
 11. Values for these conditions are examples of the I_{CC} formula. These limits are specified but not tested.



Switching Characteristics Over the Operating Range

		FCT157T		FCT157AT			FCT157CT				
		Comme	Commercial		mercial Military Commercial		Commercial			Fig	
Parameter	Description	Min. ^[12]	Max.	Min. ^[12]	Max.	Min. ^[12]	Max.	Min. ^[12]	Max.	Unit	Fig. No. ^{[13}
t _{PLH} t _{PHL}	Propagation Delay I to Y	1.5	6.0	1.5	5.8	1.5	5.0	1.5	4.3	ns	1, 3
t _{PLH} t _{PHL}	Propagation Delay E to Y	1.5	10.5	1.5	7.4	1.5	6.0	1.5	4.8	ns	1, 5
t _{PLH} t _{PHL}	Propagation Delay S to Y	1.5	10.5	1.5	8.1	1.5	7.0	1.5	5.2	ns	1, 3

Ordering Information

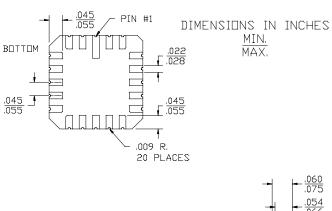
Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
4.3	CY74FCT157CTQCT	Q1	16-Lead (150-Mil) QSOP	Commercial
	CY74FCT157CTSOC/SOCT	S1	16-Lead (300-Mil) Molded SOIC	
5.0	CY74FCT157ATQCT	Q1	16-Lead (150-Mil) QSOP	Commercial
	CY74FCT157ATSOC/SOCT	S1	16-Lead (300-Mil) Molded SOIC	
5.8	CY54FCT157ATLMB	L61	20-Pin Square Leadless Chip Carrier	Military

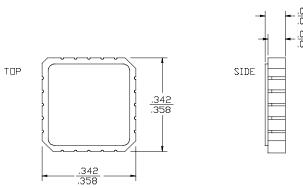
Note:

- Minimum limits are specified but not tested on Propagation Delays.
 See "Parameter Measurement Information" in the General Information Section

Document #: 38-00288-C **Package Diagrams**

20-Pin Square Leadless Chip Carrier L61 MIL-STD-1835 C-2A

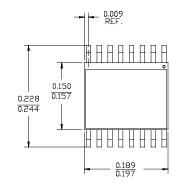


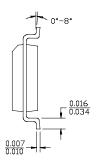


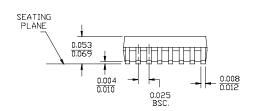


Package Diagrams (continued)

16-Lead Quarter Size Outline Q1

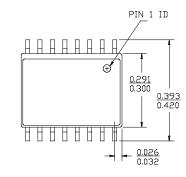




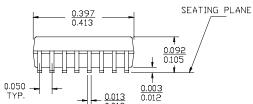


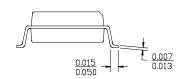
DIMENSIONS IN INCHES $\frac{\text{MIN.}}{\text{MAX.}}$ LEAD COPLANARITY 0.004 MAX.

16-Lead Molded SOIC S1



DIMENSIONS IN INCHES $\frac{\text{MIN.}}{\text{MAX.}}$ LEAD COPLANARITY 0.004 MAX.





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